

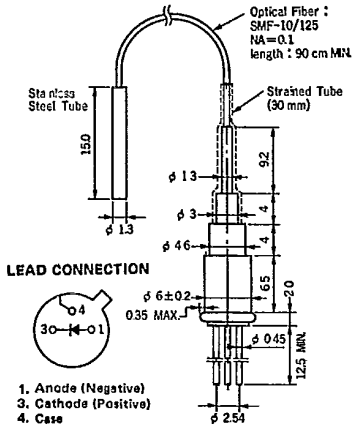
**1 300 nm OPTICAL FIBER COMMUNICATIONS**  
**φ 30 μm GERMANIUM AVALANCHE PHOTO DIODE MODULE**

**DESCRIPTION**

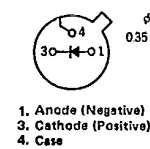
NDL5102P is a Germanium Avalanche Photo diode with singlemode fiber, especially designed for a detector of long wave-length fiber transmission systems. It features small dark current and high speed response due to small detecting area size.

**PACKAGE DIMENSIONS**

in millimeters



**LEAD CONNECTION**



- 1. Anode (Negative)
- 3. Cathode (Positive)
- 4. Case

**FEATURES**

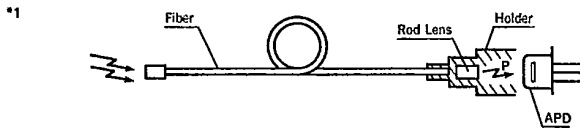
- Small dark current.  $I_D = 80 \text{ nA}$
- High sensitivity.  $\eta = 75\% @ 1300 \text{ nm}$
- Singlemode fiber pagtail.
- Detecting area size  $\phi 30 \mu\text{m}$

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

Forward Current	$I_F$	50	mA
Reverse Current	$I_R$	0.5	mA
Operating Case Temperature	$T_C$	-30 to +60	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to +70	$^\circ\text{C}$

**ELECTRO-OPTICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Reverse Breakdown Voltage	$V_{(BR)R}$	30	35	45	V	$I_D = 100 \mu\text{A}$
Dark Current	$I_D$		80	200	nA	$V_R = V_{(BR)R} \times 0.9$
Terminal Capacitance	$C_t$		0.9	1.5	pF	$V_R = 20 \text{ V}, f = 1.0 \text{ MHz}$
Quantum Efficiency	$\eta * 1$	70	75		%	$\lambda = 1300 \text{ nm}$
Sensitivity	$S * 1$	0.73	0.78		A/W	$\lambda = 1300 \text{ nm}$
Multiplication Factor	M	30	50			$\lambda = 1300 \text{ nm}, R_L = 100 \Omega, I_{po} = 1.0 \mu\text{A}, V_R = V_{(BR)R} \times 0.9$
Rise Time	$t_r$		0.3	0.8	ns	$\lambda = 1300 \text{ nm}, M = 10, R_L = 50 \Omega, I_{po} = 10 \mu\text{A}, 10-90\%$
Fall Time	$t_f$		0.3	0.8	ns	$\lambda = 1300 \text{ nm}, M = 10, R_L = 50 \Omega, I_{po} = 10 \mu\text{A}, 90-10\%$
Excess Noise Factor	x		0.95			$\lambda = 1300 \text{ nm}, M = 10, I_{po} = 1.0 \mu\text{A}, f = 30 \text{ MHz}, B = 1.0 \text{ MHz}$



" $\eta = 70\% \text{ MIN. @ } 1300 \text{ nm}$ " is guaranteed with the optical output power from a rod lens (P) in the holder.

$$\eta = \frac{h\nu}{q} \cdot \frac{I_p}{P} = \frac{h\nu}{q} \cdot S$$

$I_p$  : Photo Current

P : Optical Output Power from internal rod lens

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TYPICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

